

Vishay Siliconix

P-Channel 40 V (D-S) MOSFET

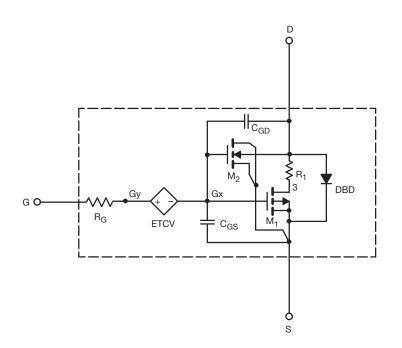
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static	<u>.</u>				
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=-~250~\mu A$	1.3	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -10.2 \text{ A}$	0.012	0.012	Ω
		V _{GS} = - 4.5 V, I _D = - 8.4 A	0.019	0.018	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10.2 A	9	10	S
Diode Forward Voltage	V _{SD}	I _S = - 8.2 A	- 0.79	- 0.80	V
Dynamic ^b	•	·			
Input Capacitance	C _{iss}	V _{DS} = - 20 V, V _{GS} = 0 V, f = 1 MHz	2990	3007	pF
Output Capacitance	C _{oss}		336	335	
Reverse Transfer Capacitance	C _{rss}		289	291	
Total Gate Charge	0	$V_{DS} = -20 V$, $V_{GS} = -10 V$, $I_D = -10.2 A$	62	64	nC
	Qg	V_{DS} = - 20 V, V_{GS} = - 4.5 V, I_D = - 10.2 A	33	33	
Gate-Source Charge	Q _{gs}		9.8	9.8	
Gate-Drain Charge	Q _{gd}		15.7	15.7	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

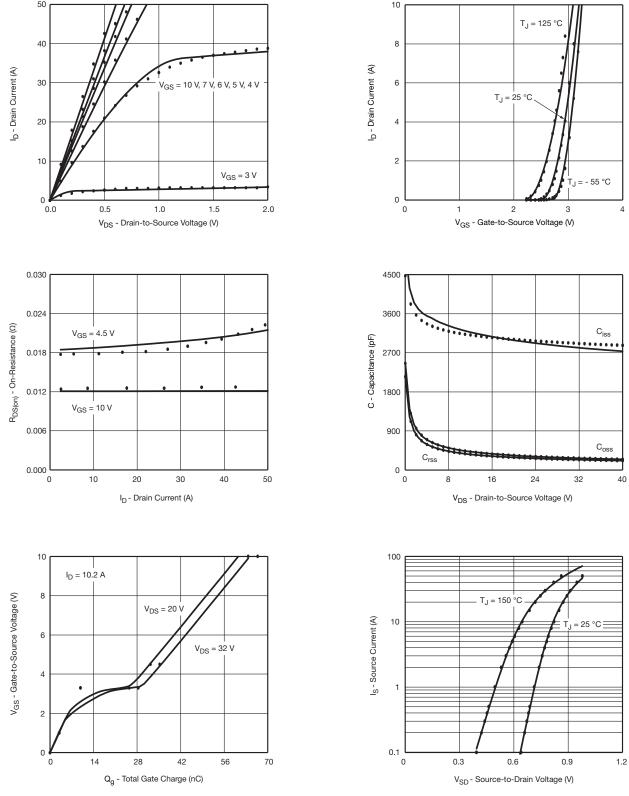
b. Guaranteed by design, not subject to production testing.



SPICE Device Model Si4401DDY

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Note

Dots and squares represent measured data.



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